

ISC Silicon NPN Power Transistor

2SD1494

DESCRIPTION

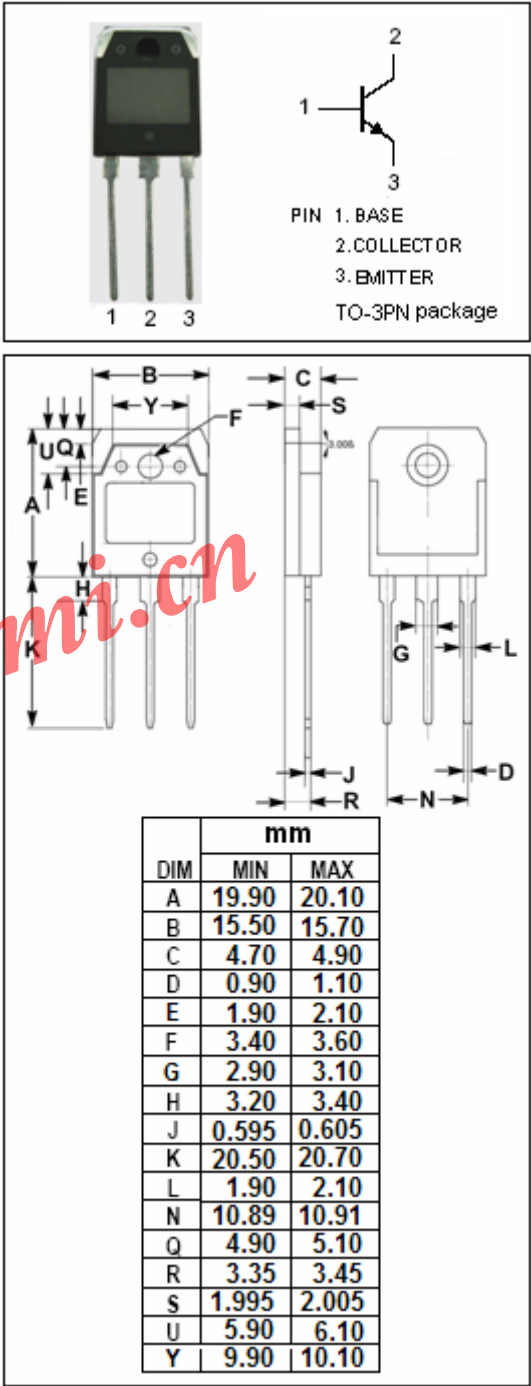
- High Breakdown Voltage-
: V_{CBO} = 1500V (Min)
- High Switching Speed

APPLICATIONS

- Designed for TV horizontal deflection output applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	1500	V
V_{CEO}	Collector-Emitter Voltage	800	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current-Continuous	3	A
I_{CM}	Collector Current-Peak	6	A
P_C	Collector Power Dissipation @ $T_C=25^{\circ}\text{C}$	50	W
T_J	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature Range	-45~150	$^{\circ}\text{C}$



ISC Silicon NPN Power Transistor**2SD1494****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C=10\text{mA}; R_{BE}=\infty$	800			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E=10\text{mA}; I_C=0$	6			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=2.5\text{A}; I_B=0.8\text{A}$			5.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=2.5\text{A}; I_B=0.8\text{A}$			1.5	V
I_{CBO}	Collector Cutoff Current	$V_{CB}=600\text{V}; I_E=0$			10	μA
t_f	Fall Time	$I_C=2.75\text{A}, I_{B1}=0.6\text{A}, I_{B2}=-1.3\text{A}$			1.0	μs

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